## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings of claims in the application:

Claim 1 (Currently Amended): An insulating material ~~used in~~ for insulating layers between electric wirings, comprising:

a borazine-silicon polymer obtained by hydrosilylation polymerization of

a borazine compound represented by chemical formula 1 possessing an alkyl group for a nitrogen atom and an alkyl group-substituted triple bond-containing organic group for a boron atom in a borazine ring, in which the boron atom has an acetylene group directly linked thereto or $R_2$ and an acetylene group jointly linked thereto; and

a silicon compound represented by chemical formula 2 possessing at least two hydrosilyl groups or a cyclic silicon compound represented by chemical formula 3 possessing at least two hydrosilyl groups; in which ~~chemical formulae~~:

$R_1$ denotes an alkyl group,

$R_2$ denotes -$(CH_2)$-m (m denoting an integer of 0 or more),

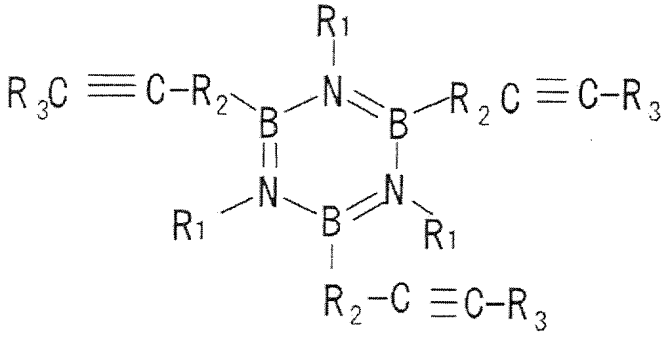
$R_3$ denotes an alkyl group linked to an acetylene group,

$R_4$ and $R_5$ each denote one identical or different monovalent group selected from the group consisting of ~~ones consisting of~~ an alkyl group, an aryl group, an aralkyl group and a hydrogen atom,

$R_6$ denotes a divalent aromatic group optionally possessing a substituent group, an oxygen atom, [[or]] a siloxane ~~including that of~~ or an oxypoly(dimethyl siloxy) group, and

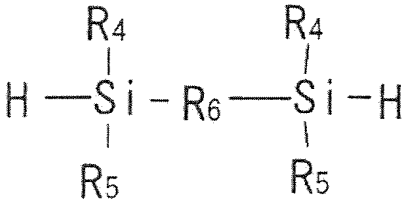
$R_7$ denotes an alkyl group, an aryl group or an aralkyl group[[.]];

wherein chemical formula 1 is as follows ~~[Chemical Formula 1]~~



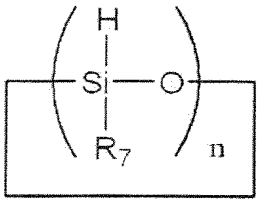
;

wherein chemical formula 2 is as follows ~~[Chemical Formula 2]~~



; and

wherein chemical formula 3 is as follows ~~[Chemical Formula 3]~~



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Claim 2 (Currently Amended): An insulating material ~~used in~~ for insulating layers between electric wirings, comprising:

a borazine-silicon polymer obtained by hydrosilylation polymerization of

~~a mixture of a borazine compound represented by Chemical Formula 4 possessing an alkyl group for a nitrogen atom and an alkyl group-substituted triple bond-containing organic group for a boron atom in a borazine ring, in which the boron atom has an acetylene group directly linked thereto or $R_2$ and an acetylene group jointly linked thereto and a borazine compound represented by Chemical Formula 5 possessing an alkyl group for a nitrogen atom and a triple bond-containing organic group not substituted by an alkyl group for a boron atom in a borazine ring, wherein the boron atom has an acetylene group directly linked thereto or $R_2$ and an acetylene group jointly linked thereto; and~~

a mixture of a first borazine compound represented by chemical formula 4 and a second borazine compound represented by chemical formula 5, the first borazine compound possessing an alkyl group for a nitrogen atom and an alkyl group-substituted triple bond-containing organic group for a boron atom in a borazine ring, in which the boron atom has an acetylene group directly linked thereto or has linked thereto R2 to which an acetylene group has been linked, the second boranzine compound possessing an alkyl group for a nitrogen atom and a triple bond-containing organic group not substituted by an alkyl group for a boron atom in a borazine ring, wherein the boron atom has an acetylene group directly linked thereto or has linked thereto R9 to which an acetylene group has been linked, the second borazine compound (formula 5) having a mixing ratio of : 90:10 to 0:100 to the first borazine compound (formula 4); and

a silicon compound represented by ~~Chemical Formula~~ chemical formula 6 possessing at least two hydrosilyl groups or a cyclic silicon compound represented by ~~Chemical Formula~~ chemical formula 7 possessing at least two hydrosilyl groups, in which ~~Chemical Formulae~~:

$R_1$ denotes an alkyl group,

$R_2$ denotes -$(CH_2)$-m (m denoting an integer of 0 or more),

$R_3$ denotes an alkyl group linked to an acetylene group,

$R_4$ and $R_5$ each denote one identical or different univalent group selected from the group ~~ones~~ consisting of an alkyl group, an aryl group, an aralkyl group and a hydrogen atom,

$R_6$ denotes a divalent aromatic group optionally possessing a substituent group, an oxygen atom, [[or ]] a siloxane ~~including that of~~ or an oxypoly(dimethyl siloxy) group,

$R_7$ denotes an alkyl group, an aryl group or an aralkyl group,

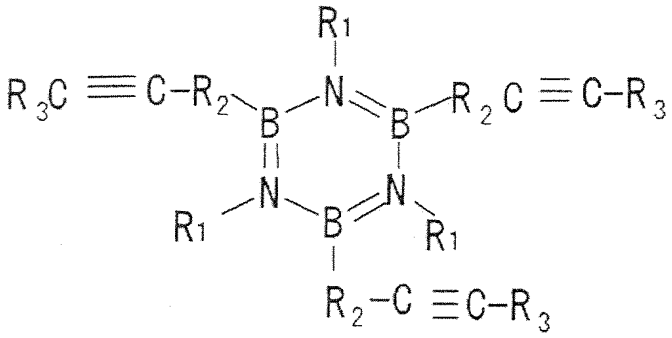
$R_8$ denotes an alkyl group,

$R_9$ denotes a methylene group, and

n denotes an integer of 3 or more[[. ]];

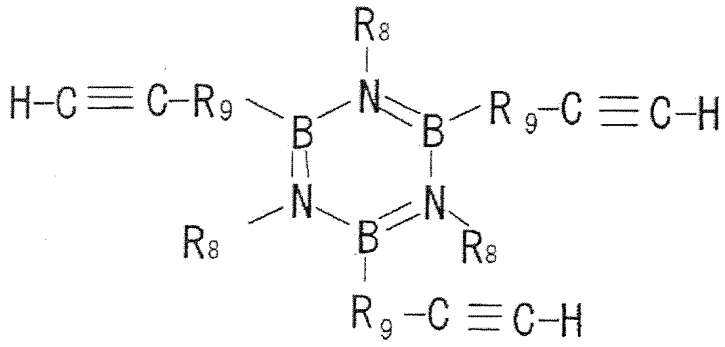
wherein chemical formula 4 is as follows

~~[Chemical Formula 4]~~



wherein chemical formula 5 is as follows

~~[Chemical Formula 5]~~



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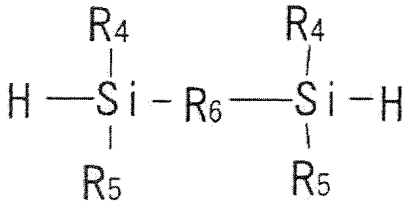
wherein chemical formula 6 is as follows

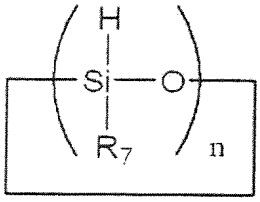
~~[Chemical Formula 6]~~



; and

wherein chemical formula 7 is as follows

~~[Chemical Formula 7]~~



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Claim 3 (Withdrawn): A semiconductor device, comprising a wiring structure provided with a first wiring layer formed on a surface of a semiconductor region forming an

active component or a passive component aimed at and a second wiring layer formed in an upper layer of the first wiring layer and also provided with a first insulating structure insulating the semiconductor region and the first wiring layer, a second insulating structure insulating a distribution interlayer formed of the first wiring layer, a third insulating structure contained in a structure electrically insulating the first wiring layer and the second wiring layer and forming connecting holes electrically connecting the first wiring layer and the second wiring layer, and a fourth insulating structure insulating a distribution interlayer formed of the second wiring layer, and further provided with a fifth insulating layer formed of the interlayer insulating material in (1) a region interposed between the first insulating structure and the fourth insulating structure relative to a direction of film thickness and excluding the connecting holes electrically connecting the first and second wiring layers relative to a plane, (2) a region interposed between the first insulating structure and the fourth insulating structure relative to the direction of film thickness and excluding the wiring by the first wiring layer relative to the plane, (3) a region disposed in a region higher than the first insulating structure relative to the direction of film thickness and excluding the connecting holes for electrically connecting the second and third wiring layers relative to the plane, or (4) a region higher than the first insulating structure relative to the direction of film thickness and excluding the wiring by the third wiring layer relative to the plane.

Claim 4 (Currently Amended): A semiconductor device, comprising:

a wiring structure ~~provided with~~ comprising

a first wiring layer formed on a surface of a semiconductor region forming an active component or a passive component, ~~aimed at~~ and

a second wiring layer formed in an upper layer of the first wiring layer,

~~also provided with~~ a first insulating structure insulating the semiconductor region and the first wiring layer,

a second insulating structure insulating an interlayer formed of the first wiring layer,

a third insulating structure contained in a structure electrically insulating the first wiring layer and the second wiring layer and forming connecting holes electrically connecting the first wiring layer and the second wiring layer, and

a fourth insulating structure insulating an interlayer formed with the second wiring layer, and ~~further incorporating~~

comprising in one of the second, third and fourth insulating structures the insulating material according to claims 1 or 2 ~~any one of claim 1 to claim 2~~.

Claim 5 (New): An insulating layer, comprising: the insulating material of Claim 1; wherein said insulating layer is between electric wirings.

Claim 6 (New): An insulating layer, comprising: the insulating material of Claim 2; wherein said insulating layer is between electric wirings.

Claim 7 (New): An ultra large scale integrated circuit (ULSI), comprising:

an USLI multilayer interconnection; and

an insulating layer between electric wirings, said insulating layer comprising the insulating material of Claim 1.

Claim 8 (New): An ultra large scale integrated circuit (ULSI), comprising:

an USLI multilayer interconnection; and

an insulating layer between electric wirings, said insulating layer comprising the insulating material of Claim 2.

## BASIS FOR THE AMENDMENT

Claims 1 and 2 have been amended as supported by the claims as originally filed and at paragraph [0077] of the specification.

New Claims 5-8 have been added.

New Claim 5 is supported by Claim 1 as originally filed.

New Claim 6 is supported by Claim 2 as originally filed.

New Claim 7 is supported by Claim 1 and the specification as originally filed.

New Claim 8 is supported by Claim 1 and the specification as originally filed.

No new matter is believed to have been added by entry of this amendment. Entry and favorable reconsideration are respectfully requested.

Upon entry of this amendment Claims 1-8 will now be active in this application. Claim 3 stands withdrawn from consideration as being drawn to non-elected subject matter.